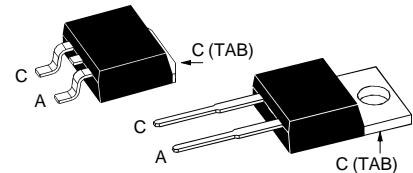


Power Schottky Rectifier

$I_{FAV} = 16 \text{ A}$
 $V_{RRM} = 100 \text{ V}$
 $V_F = 0.64 \text{ V}$

| V_{RSM} | V_{RRM} | Type |
|-----------|-----------|-------------|
| V | V | |
| 100 | 100 | DSS 16-01A |
| | | DSS 16-01AS |

TO-263 AB
(AS-Type)

A = Anode, C = Cathode , TAB = Cathode

| Symbol | Conditions | Maximum Ratings | |
|----------------|---|-----------------|------------------------|
| I_{FRMS} | | 35 | A |
| I_{FAV} | $T_C = 155^\circ\text{C}$; rectangular, $d = 0.5$ | 16 | A |
| I_{FSM} | $T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sinev | 230 | A |
| E_{AS} | $I_{AS} = 9.5 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive | 10 | mJ |
| I_{AR} | $V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive | 1 | A |
| $(dv/dt)_{cr}$ | | 5000 | $\text{V}/\mu\text{s}$ |
| T_{VJ} | | -55...+175 | $^\circ\text{C}$ |
| T_{VJM} | | 175 | $^\circ\text{C}$ |
| T_{stg} | | -55...+150 | $^\circ\text{C}$ |
| P_{tot} | $T_C = 25^\circ\text{C}$ | 105 | W |
| M_d | mounting torque (A-Type only) | 0.4...0.6 | Nm |
| Weight | typical | 2 | g |

| Symbol | Conditions | Characteristic Values | |
|--------------------------|--|-----------------------|-------------------|
| | | typ. | max. |
| I_R ① | $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$ | 0.5 5 | mA mA |
| V_F | $I_F = 15 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 15 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ | 0.64 0.79 0.76 | V V V |
| R_{thJC} R_{thCH} | | 0.5 | 1.4 K/W K/W |

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

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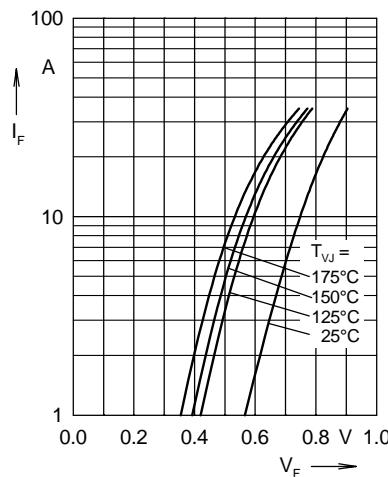


Fig. 1 Maximum forward voltage drop characteristics

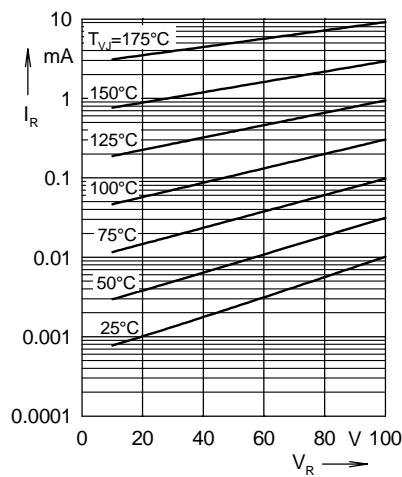


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

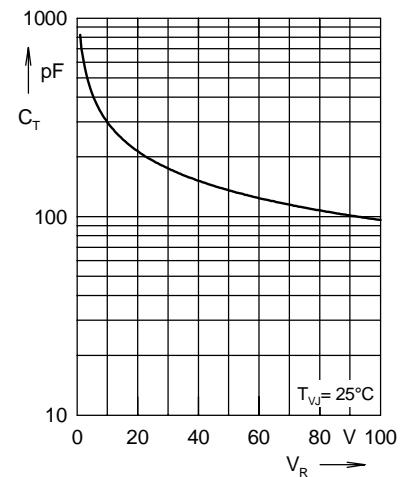


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

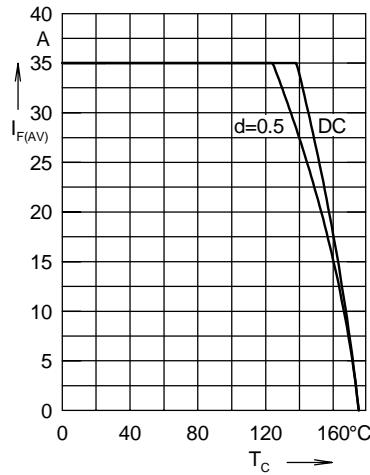


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

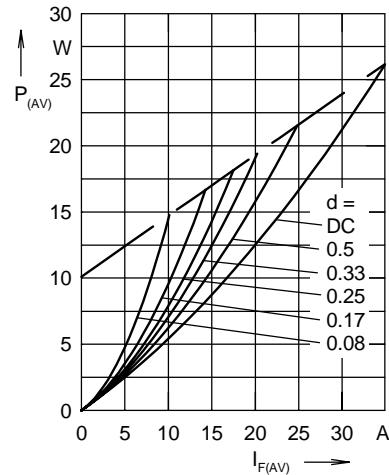


Fig. 5 Forward power loss characteristics

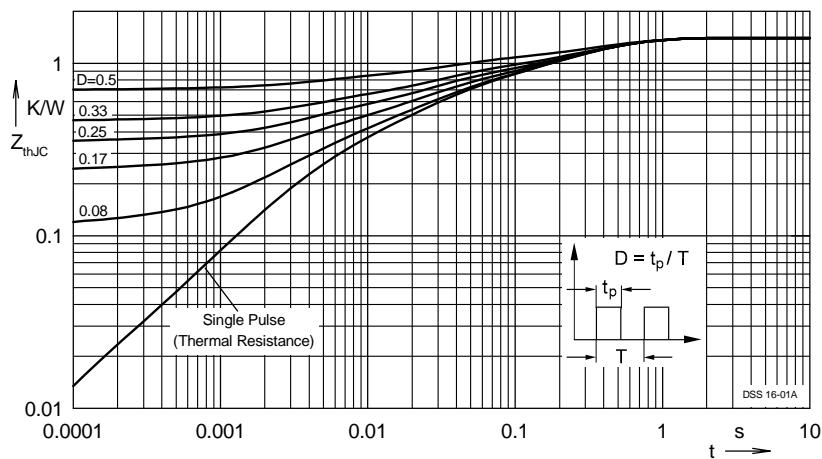


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode